

MPSW42

Preferred Device

One Watt High Voltage Transistor

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Collector-Base Voltage	V_{CBO}	300	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 20	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

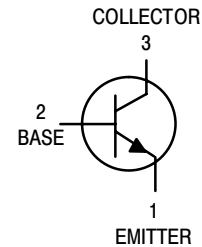
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

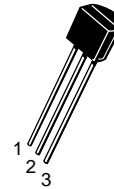


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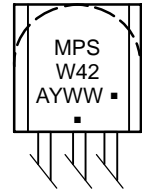
<http://onsemi.com>



MARKING DIAGRAM



TO-92
CASE 29-11
STYLE 1



MPSW42 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MPSW42	TO-92	5,000 Units/Box
MPSW42G	TO-92 (Pb-Free)	5,000 Units/Box
MPSW42RLRA	TO-92	2,000/Tape & Reel
MPSW42RLRAG	TO-92 (Pb-Free)	2,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MPSW42

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	300	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = 100 μA _{dc} , I _E = 0)	V _{(BR)CBO}	300	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 100 μA _{dc} , I _C = 0)	V _{(BR)EBO}	6.0	–	V _{dc}
Collector Cutoff Current (V _{CB} = 200 V _{dc} , I _E = 0)	I _{CBO}	–	0.1	μA _{dc}
Emitter Cutoff Current (V _{EB} = 6.0 V _{dc} , I _C = 0)	I _{EBO}	–	0.1	μA _{dc}
ON CHARACTERISTICS				
DC Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 30 mA _{dc} , V _{CE} = 10 V _{dc})	h _{FE}	25 40 40	– – –	–
Collector–Emitter Saturation Voltage (I _C = 20 mA _{dc} , I _B = 2.0 mA _{dc})	V _{CE(sat)}	–	0.5	V _{dc}
Base–Emitter Saturation Voltage (I _C = 20 mA _{dc} , I _B = 2.0 mA _{dc})	V _{BE(sat)}	–	0.9	V _{dc}
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product (I _C = 10 mA _{dc} , V _{CE} = 20 V _{dc} , f = 20 MHz)	f _T	50	–	MHz
Collector Capacitance (V _{CB} = 20 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{cb}	–	3.0	pF

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

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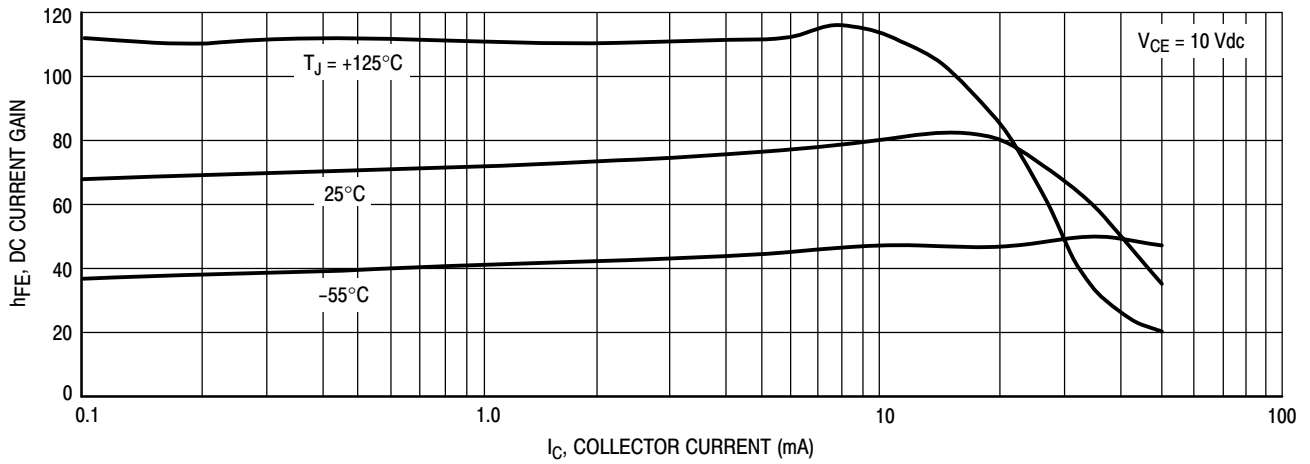


Figure 1. DC Current Gain

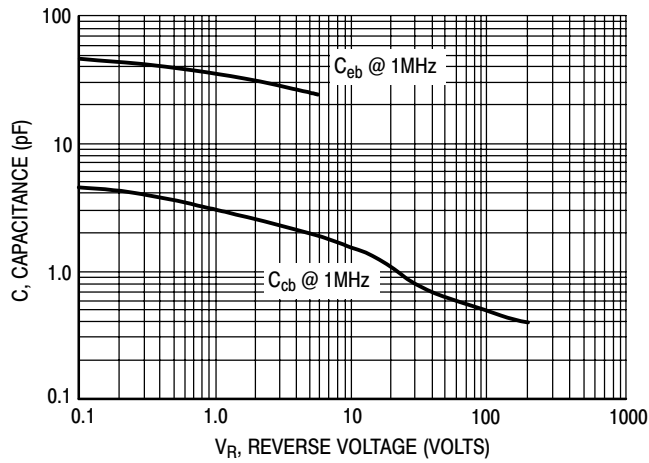


Figure 2. Capacitance

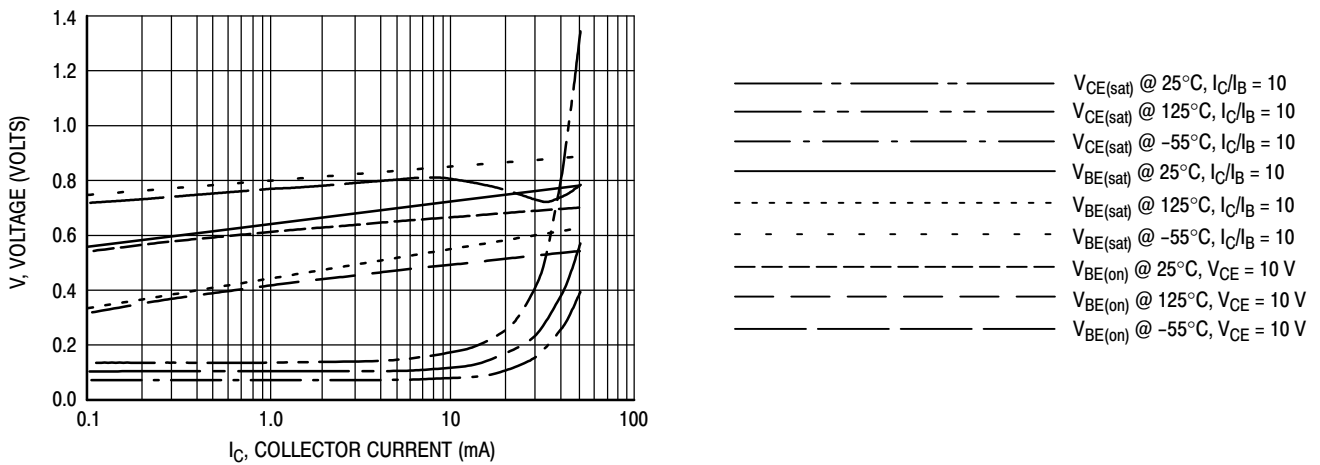
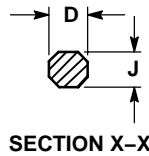
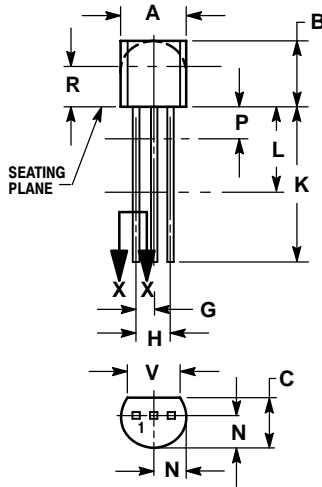


Figure 3. "ON" Voltages

MPSW42

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

1. PIN 1. EMITTER
2. BASE
3. COLLECTOR

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